TOSHIBA TRANSISTOR SILICON, SILICON GERMANIUM NPN EPITAXIAL PLANAR TYPE

MT6L76FS

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

Two devices are built in to the fine pich small mold package (6pins):fs6

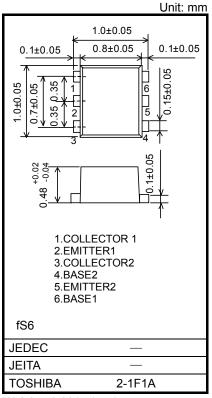
• It exsels in the buffer and oscillation use.

Mounted Devices

	Q1	Q2
Three-pin fSM mold products are corresponded	MT3S06FS	MT3S106FS

Absolute Maximum Ratings (Ta = 25°C)

CHARACTERISTICS	SYMBOL	RAT	UNIT	
		Q1	Q2	OIVIT
Collector-Base Voltage	V _{CBO}	10	13	V
Collector-Emitter Voltage	V _{CEO}	5	6	>
Emitter-Base Voltage	V _{EBO}	1.5	1	>
Collector Current	IC	15	80	mA
Base Current	ΙΒ	7	20	mA
Collector power dissipation	P _C (Note 1)	10	mW	
		110 (Note 2)		
Junction temperature	Tj	125		°C
Storage temperature range	T _{stg}	-55~125		°C



Weight: 0.001g (typ.)

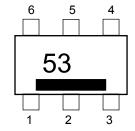
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

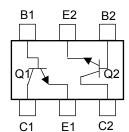
Note 1 : 1.0 cm 2 × 1.0 mm (t) at the time of glass epoxy printed circuit board mounting.

Note 2: At the time of two-element operation

Marking (top view)



Pin Assignment (top view)



ELECTRICAL CHARACTERISTICS Q1 (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I _{CBO}	V _{CB} = 5 V, I _E = 0	_	_	0.1	μА	
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0		_	1	μА	
DC Current Gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	70	_	140	_	
Reverse Transfer Capacitance	C _{re} (Note)	$V_{CB} = 1 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	0.25	0.5	pF	
Transition Frequency	f _T	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA}$	7	10	_	GHz	
Insertion Gain	S _{21e} ² (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	8.5	_	40	
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 7 \text{ mA}, f = 2 \text{ GHz}$	7	9.5	_	dB	
Noise Figure	NF	$V_{CE} = 1 \text{ V}, I_{C} = 3 \text{ mA}, f = 2 \text{ GHz}$	_	1.7	3	dB	

ELECTRICAL CHARACTERISTICS Q2 (Ta = 25°C)

CHARACTERISTICS	SYMBOL	CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I _{CBO}	$V_{CB} = 5 \text{ V}, I_{E} = 0$	_	_	0.1	μА	
Emitter Cut-off Current	I _{EBO}	V _{EB} = 1 V, I _C = 0	_	_	0.5	μΑ	
DC Current Gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	110	_	160	_	
Reverse Transfer Capacitance	C _{re} (Note)	V _{CB} = 1 V, I _E = 0, f = 1 MHz	_	0.5	0.7	pF	
Transition Frequency	f _T	V _{CE} = 1 V, I _C = 10 mA	6.5	8.5	_	GHz	
Insertion Gain	S _{21e} ² (1)	V _{CE} = 1 V, I _C = 10 mA, f = 2 GHz	_	8	_	40	
	S _{21e} ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 2 \text{ GHz}$	8.5	10	_	dB	
Noise Figure	NF	V _{CE} = 1 V, I _C = 10 mA, f = 2 GHz	_	1.2	2	dB	

Note: Cre is measured by 3 terminal method capacitance bridge.

Caution

This device is sensitive to electrostatic discharge due to applied the high frequency transistor process of fT=60GHz class is used for this product.

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Please make enough tool and equipment earthed when you handle.

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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